

BDX54/A/B/C

Hammer Drivers, Audio Amplifiers Applications Power Liner and Switching Applications

- Power Darlington TR
- Complement to BDX53, BDX53A, BDX53B and BDX53C respectively



1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage : BDX54	- 45	V	
	: BDX54A	- 60	V	
	: BDX54B	- 80	V	
	: BDX54C	- 100	V	
V _{CEO}	Collector-Emitter Voltage : BDX54	- 45	V	
	: BDX54A	- 60	V	
	: BDX54B	- 80	V	
	: BDX54C	- 100	V	
V _{EBO}	Emitter-Base Voltage	- 5	V	
I _C	Collector Current (DC)	- 8	А	
I _{CP}	*Collector Current (Pulse)	- 12	Α	
I _B	Base Current	- 0.2	Α	
P _C	Collector Dissipation (T _C =25°C)	60	W	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 65 ~ 150	°C	

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaining Voltage					
	: BDX54	$I_C = -100 \text{mA}, I_B = 0$	- 45			V
	: BDX54A		- 60			V
	: BDX54B		- 80			V
	: BDX54C		- 100			V
I _{CBO}	Collector Cut-off Current : BDX54	$V_{CB} = -45V, I_{E} = 0$			- 200	μΑ
	: BDX54A	$V_{CB} = -60V, I_{E} = 0$			- 200	μΑ
	: BDX54B	$V_{CB} = -80V, I_{E} = 0$			- 200	μΑ
	: BDX54C	$V_{CB} = -100V, I_{E} = 0$			- 200	μΑ
I _{CEO}	Collector Cut-off Current : BDX54	$V_{CE} = -22V, I_{B} = 0$			- 500	μΑ
	: BDX54A	$V_{CE} = -30V, I_{B} = 0$			- 500	μΑ
	: BDX54B	$V_{CE} = -40V, I_{B} = 0$			- 500	μΑ
	: BDX54C	$V_{CE} = -50V, I_{B} = 0$			- 500	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2	mA
h _{FE}	* DC Current Gain	$V_{CE} = -3V, I_{C} = -3A$	750			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = -3A, I_B = -12mA$			- 2	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	$I_C = -3A, I_B = -12mA$			- 2.5	V
V _F	* Parallel Diode Forward Voltage	I _F = - 3A		- 1.8	- 2.5	V
		I _F = - 8A		- 2.5		V

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Typical Characteristics

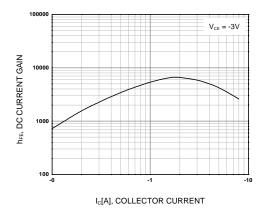


Figure 1. DC current Gain

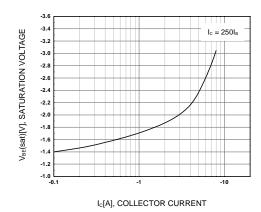


Figure 2. Base-Emitter Saturation Voltage

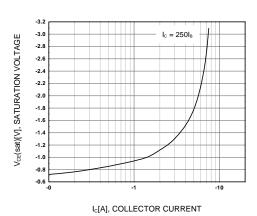


Figure 3. Collector-Emitter Saturation Voltage

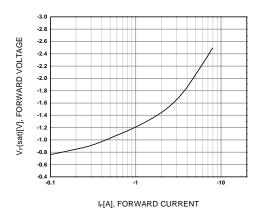


Figure 4. Damper Diode Forward Voltage

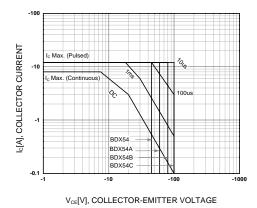


Figure 5. Safe Operating Area

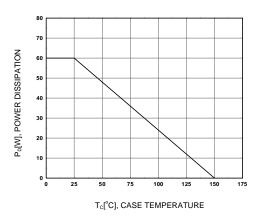
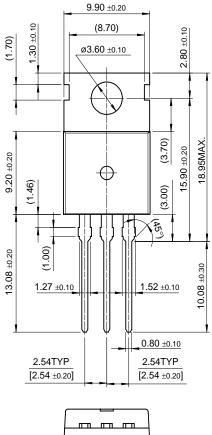


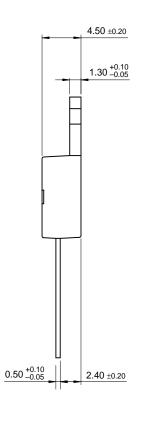
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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